



National Semiconductor

January 1988

MM54HC05/MM74HC05 Hex Inverter (Open Drain)

MM54HC05/MM74HC05 Hex Inverter (Open Drain)

General Description

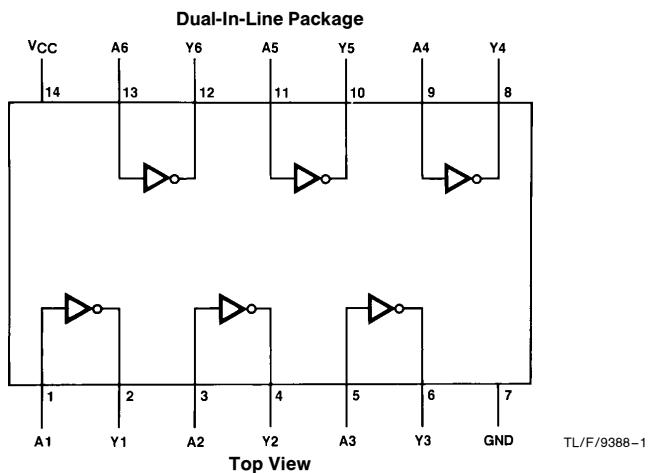
The MM54HC05/MM74HC05 are logic functions fabricated by using advanced silicon-gate CMOS technology, which provides the inherent benefits of CMOS—low quiescent power and wide power supply range. These devices are also functionally and pin-out compatible with standard DM54LS/DM74LS logic families. The MM54HC05/MM74HC05 open drain Hex Inverter requires the addition of an external resistor to perform a wire-NOR function.

All inputs are protected from static discharge damage by internal diodes to V_{CC} and ground.

Features

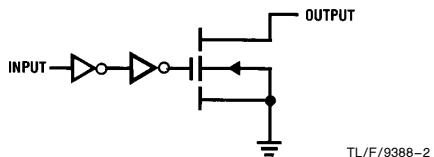
- Open drain for wire-NOR function
- Fanout of 10 LS-TTL loads
- Typical propagation delays:
 - t_{PZL} (with 1 kΩ resistor) 8 ns
 - t_{PLZ} (with 1 kΩ resistor) 13 ns
- Low input current: 1 μA maximum

Connection Diagram

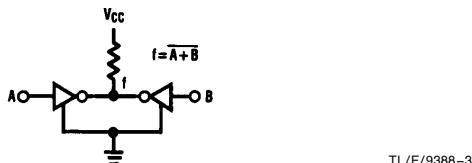


Order Number MM54HC05 or MM74HC05

Logic Diagram



Typical Application



Note: Can be extended to more than 2 inputs.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	$-0.5V$ to $+7.0V$
DC Input Voltage (V_{IN})	$-1.5V$ to $V_{CC} + 1.5V$
DC Output Voltage (V_{OUT})	$-0.5V$ to $V_{CC} + 0.5V$
Clamp Diode Current (I_{IK}, I_{OK})	$\pm 20\text{ mA}$
DC Output Current, per pin (I_{OUT})	$\pm 25\text{ mA}$
DC V_{CC} or GND Current, per pin (I_{CC})	$\pm 50\text{ mA}$
Storage Temperature Range (T_{STG})	-65°C to $+150^{\circ}\text{C}$
Power Dissipation (P_D) (Note 3) S.O. Package only	600 mW 500 mW
Lead Temperature (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A) MM74HC	-40	$+85$	°C
MM54HC	-55	$+125$	°C
Input Rise or Fall Times (t_r, t_f)	$V_{CC} = 2.0V$		
	1000 ns		
	$V_{CC} = 4.5V$		
	500 ns		
	$V_{CC} = 6.0V$		
	400 ns		

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^{\circ}\text{C}$		74HC	54HC	Units
				Typ		$T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	$T_A = -55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	
V_{IH}	Minimum High Level Input Voltage		2.0V 4.5V 6.0V	1.5 3.15 4.2		1.5 3.15 4.2	1.5 3.15 4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V	0.5 1.35 1.8		0.5 1.35 1.8	0.5 1.35 1.8	V
V_{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT} \leq 20\text{ }\mu\text{A}$ $R_L = \infty$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ $ I_{OUT} \leq 4.0\text{ mA}$ $ I_{OUT} \leq 5.2\text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
I_{LKG}	Maximum High Level Output Leakage Current	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$	6.0V		0.5	5	10	μA
I_{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\text{ }\mu\text{A}$	6.0V		2.0	20	40	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: $-12\text{ mW}/^{\circ}\text{C}$ from 65°C to 85°C ; ceramic "J" package: $-12\text{ mW}/^{\circ}\text{C}$ from 100°C to 125°C .

Note 4: For a power supply of $5V \pm 10\%$ the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

** V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC}=5V$, $T_A=25^\circ C$, $C_L=15\text{ pF}$, $t_r=t_f=6\text{ ns}$

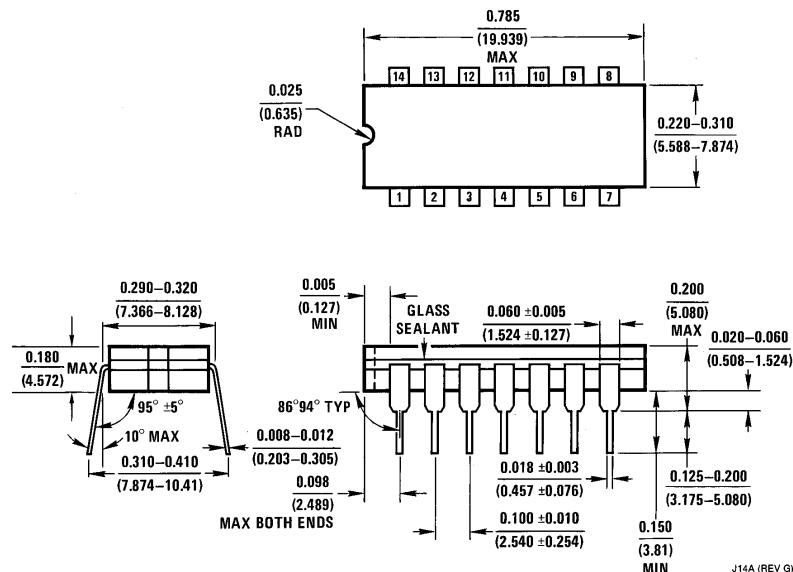
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t _{PZL} , t _{PLZ}	Maximum Propagation Delay	R _L = 1 kΩ	8		ns

AC Electrical Characteristics $V_{CC} = 2.0V$ to $6.0V$, $C_L = 50\text{ pF}$, $t_r = t_f = 6\text{ ns}$ unless otherwise specified

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C		74HC	54HC	Units
				Typ	Guaranteed Limits			
t _{PZL}	Maximum Propagation Delay	R _L = 1 kΩ	2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
t _{PLZ}	Maximum Propagation Delay	R _L = 1 kΩ	2.0V	30	90	115	135	ns
			4.5V	13	18	23	27	ns
			6.0V	12	15	20	23	ns
t _{THL}	Maximum Output Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C _{PD}	Power Dissipation Capacitance (Note 5)	(per gate)		8				pF
C _{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$. The power dissipated by R_L is not included.

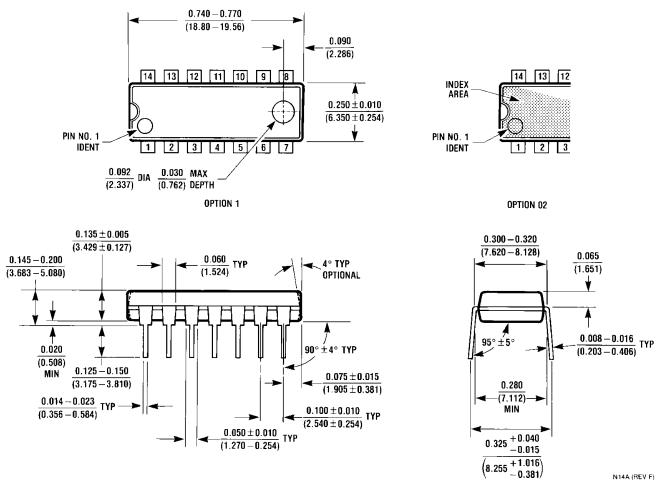
Physical Dimensions inches (millimeters)



**Order Number MM54HC05J or MM74HC05J
NS Package Number J14A**

MM54HC05/MM74HC05 Hex Inverter (Open Drain)

Physical Dimensions inches (millimeters) (Continued)



**Order Number MM74HC05N
NS Package Number N14A**

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



**National Semiconductor
Corporation**
1111 West Bardin Road
Arlington, TX 76017
Tel: (800) 272-9959
Fax: (800) 737-7018

**National Semiconductor
Europe**
Fax: (+49) 0-180-530 85 86
Email: cnjwge@tevm2.nsc.com
Deutsch Tel: (+49) 0-180-530 85 85
English Tel: (+49) 0-180-532 78 32
Français Tel: (+49) 0-180-532 93 58
Italiano Tel: (+49) 0-180-534 16 80

**National Semiconductor
Hong Kong Ltd.**
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd.
Tsimshatsui, Kowloon
Hong Kong
Tel: (852) 2737-1600
Fax: (852) 2736-9960

**National Semiconductor
Japan Ltd.**
Tel: 81-043-299-2309
Fax: 81-043-299-2408

National does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and National reserves the right at any time without notice to change said circuitry and specifications.